innodisk

Total Solution For Industrial Flash Storage

M.2 (P42)

3TE6 Series

Customer: _____

Customer Part Number: _____

Innodisk Part Number: _____

Innodisk Model Name: _____

Date: _____

Innodisk Approver	Customer Approver

Table of contents

1. PRODUCT OVERVIEW 7
1.1 Introduction of Innodisk M.2 (P42) 3TE6 7
1.2 Product View and Models 7
1.3 PCIe Interface 7
2. PRODUCT SPECIFICATIONS 8
2.1 Capacity and Device Parameters 8
2.2 Performance 8
2.3 Electrical Specifications 9
2.3.1 Power Requirement 9
2.3.2 Power Consumption 9
2.4 Environmental Specifications 9
2.4.1 Temperature Ranges 9
2.4.2 Humidity 9
2.4.3 Shock and Vibration 9
2.4.4 Mean Time between Failures (MTBF) 10
2.5 CE and FCC Compatibility 10
2.6 RoHS Compliance 10
2.7 Reliability 11
2.8 Transfer Mode 11
2.9 Pin Assignment 12
2.10 Mechanical Dimensions 14
2.11 Assembly Weight 14
2.12 Seek Time 14
2.13 NAND Flash Memory 14
2.14 Heat-Dissipating Copper Foil 14
3. THEORY OF OPERATION 15
3.1 Overview 15
3.2 PCIe Gen III x 4 Controller 15
3.3 Error Detection and Correction 16
3.4 Wear-Leveling 16
3.5 Bad Blocks Management 16
3.6 Garbage Collection/TRIM 16
3.7 End to End Data Path Protection 16
3.8 Thermal Management 17
3.9 AES function (Optional) 17
4. INSTALLATION REQUIREMENTS 17
4.1 M.2 (P42) 3TE6 Pin Directions 17

4.2 ELECTRICAL CONNECTIONS FOR M.2 (P42) 3TE6 17
4.3 DEVICE DRIVE 18
5. SMART / HEALTH INFORMATION 19
5.1 GET LOG PAGE(LOG IDENTIFIER 02H) 19
6. PART NUMBER RULE 24
7. APPENDIX 25

REVISION HISTORY

Revision	Description	Date
Preliminary 0.1	First release	Apr., 2020
Preliminary 0.2	Performance & Power Consumption Remark Update	June, 2020
Preliminary 0.3	Update 2.14 Mechanical Information	July, 2020

List of Tables

TABLE 1: DEVICE PARAMETERS 8
TABLE 2: PERFORMANCE 8
TABLE 3: INNODISK M.2 (P42) 3TE6 POWER REQUIREMENT 9
TABLE 4: POWER CONSUMPTION 9
TABLE 5: TEMPERATURE RANGE FOR M.2 (P42) 3TE6 9
TABLE 6: SHOCK/VIBRATION TESTING FOR M.2 (P42) 3TE6 9
TABLE 7: M.2 (P42) 3TE6 MTBF 10
TABLE 8: M.2 (P42) 3TE6 TBW 11
TABLE 9: INNODISK M.2 (P42) 3TE6 PIN ASSIGNMENT 12
TABLE 10: GET LOG PAGE – SMART / HEALTH INFORMATION LOG 19

List of Figures

FIGURE 1: INNODISK M.2 (P42) 3TE6 (TYPE 2280) 7
FIGURE 2: INNODISK M.2 (P42) 3TE6 DIAGRAM 14
FIGURE 3: INNODISK M.2 (P42) 3TE6 BLOCK DIAGRAM 15
FIGURE 4: SIGNAL SEGMENT AND POWER SEGMENT 17

1. Product Overview

1.1 Introduction of Innodisk M.2 (P42) 3TE6

Innodisk M.2 (P42) 3TE6 is a NVM Express DRAM-less SSD designed with PCIe interface and industrial 3D TLC NAND Flash. M.2 (P42) 3TE6 supports PCIe Gen III x 4 and it is compliant with NVM 1.3 providing excellent top and also sustained performance. With sophisticated error detection and correction (ECC) functions, the module can ensure full End-to-End data path protection that secures the data transmission between host system and NAND Flash. In addition, with embedded AES-256 bit engine, your data can be further secured.

1.2 Product View and Models

Innodisk M.2 (P42) 3TE6 is available in follow capacities with industrial 3D TLC flash ICs.

M.2 (P42) 3TE6 64GB
M.2 (P42) 3TE6 128GB
M.2 (P42) 3TE6 256GB
M.2 (P42) 3TE6 512GB

TBD

Figure 1: Innodisk M.2 (P42) 3TE6 (type 2242)

1.3 PCIe Interface

Innodisk M.2 (P42) 3TE6 supports PCIe Gen III interface and compliant with NVMe 1.3. M.2 (P42) 3TE6 can work under PCIe Gen 1, Gen 2 and Gen 3.

Most of operating system includes NVMe in-box driver now. For more information about the driver support in each OS, please visit http://nvmexpress.org/resources/drivers.

2. Product Specifications

2.1 Capacity and Device Parameters

M.2 (P42) 3TE6 device parameters are shown in Table 1.

Table 1: Device parameters

Capacity	LBA	User Capacity(MB)
64GB	117231408	57242
128GB	234441648	114473
256GB	468862128	228937
512GB	937703088	457863

2.2 Performance

Burst Transfer Rate: 4 GB/s

Table 2: Performance*

Capacity	64GB	128GB	256GB	512GB
Sequential** Read (Q4T1)	700 MB/s	1,250 MB/s	1,550 MB/s	1,650 MB/s
Sequential** Write (Q4T1)	85 MB/s	500 MB/s	1,000 MB/s	1,600MB/s
Sustained Sequential Write (Avg.) ***	75 MB/s	160 MB/s	330 MB/s	620 MB/s
4KB Random** Read (QD32)	38,000	78,000	120,000	130,000
4KB Random** Write (QD32)	20,000	48,000	95,000	97,000

Note: * Performance results are measured in Room Temperature with Out-of-Box devices and may vary depending on overall system setup.

Note: ** Performance results are based on CrystalDiskMark 5.1.2 with file size 1000MB.

Note: *** Performance results are based on AIDA 64 with block size 1MB of Linear Write Test Item

2.3 Electrical Specifications

2.3.1 Power Requirement

Table 3: Innodisk M.2 (P42) 3TE6 Power Requirement

Item	Symbol	Rating	Unit
Input voltage	V_{IN}	+3.3 DC +- 5%	V

2.3.2 Power Consumption

Table 4: Power Consumption*

Mode	Power Consumption (mA)			
	64GB	128GB	256GB	512GB
Read (RMS)	520	625	690	775
Write (RMS)	500	500	700	990
Idle (RMS)	230	230	230	230
Power On Peak	630	780	830	890

Note: * Current results may vary depending on system components and power circuit design.

2.4 Environmental Specifications

2.4.1 Temperature Ranges

Table 5: Temperature range for M.2 (P42) 3TE6

Temperature	Range
Operating	Standard Grade: 0°C to +70°C Industry Grade: -40°C to +85°C
Storage	-55°C to +95°C

2.4.2 Humidity

Relative Humidity: 10-95%, non-condensing

2.4.3 Shock and Vibration

Table 6: Shock/Vibration Testing for M.2 (P42) 3TE6

Reliability	Test Conditions	Reference Standards
Vibration	7 Hz to 2K Hz, 20G, 3 axes	IEC 60068-2-6
Mechanical Shock	Duration: 0.5ms, 1500 G, 3 axes	IEC 60068-2-27

2.4.4 Mean Time between Failures (MTBF)

Table 7 summarizes the MTBF prediction results for various M.2 (P42) 3TE6 configurations. The analysis was performed using a RAM Commander™ failure rate prediction.

- **Failure Rate**: The total number of failures within an item population, divided by the total number of life units expended by that population, during a particular measurement interval under stated condition.
- **Mean Time between Failures (MTBF)**: A basic measure of reliability for repairable items: The mean number of life units during which all parts of the item perform within their specified limits, during a particular measurement interval under stated conditions.

Table 7: M.2 (P42) 3TE6 MTBF

Product	Condition	MTBF (Hours)
Innodisk M.2 (P42) 3TE6	Telcordia SR-332 GB, 25°C	>3,000,000

2.5 CE and FCC Compatibility

M.2 (P42) 3TE6 conforms to CE and FCC requirements.

2.6 RoHS Compliance

M.2 (P42) 3TE6 is fully compliant with RoHS directive.

2.7 Reliability

Table 8: M.2 (P42) 3TE6 TBW

Parameter	Value
Read Cycles	Unlimited Read Cycles
Flash endurance	3,000 P/E cycles
Wear-Leveling Algorithm	Support
Bad Blocks Management	Support
Error Correct Code	Support(LDPC)
Data Retention	Under 40°C: 10 Years at Initial NAND Status (PE cycles under 100) 1 Year at NAND Life End (PE cycles reach 3,000)

TBW* (Total Bytes Written) Unit: TB

Capacity	Sequential workload	Client workload
64GB	148 TBW	39 TBW
128GB	296 TBW	119 TBW
256GB	593 TBW	274 TBW
512GB	1186 TBW	552 TBW

* Note:

1. Sequential: Mainly sequential write, tested by Vdbench. These are estimated values subject to update.
2. Client: Follow JESD218 Test method and JESD219A Workload, tested by ULINK. (The capacity lower than 64GB client workload is not specified in JEDEC219A, the values are estimated.)
3. Based on out-of-box performance.
4. Current TBW Values are for reference only. Acute figures will be released after MP.

2.8 Transfer Mode

M.2 (P42) 3TE6 support following transfer mode:

PCIe Gen III 4 GB/s

PCIe Gen II 2 GB/s

PCIe Gen I 1 GB/s

2.9 Pin Assignment

Innodisk M.2 (P42) 3TE6 follows standard M.2 spec, socket 3 key M PCIe-based SSD pinout. See Table 9 for M.2 (P42) 3TE6 pin assignment.

Table 9: Innodisk M.2 (P42) 3TE6 Pin Assignment

Signal Name	Pin #	Pin #	Signal Name
		75	GND
3.3V	74	73	GND
3.3V	72	71	GND
3.3V	70	69	NC
NC	68	67	NC
Notch	66	65	Notch
Notch	64	63	Notch
Notch	62	61	Notch
Notch	60	59	Notch
NC (Reserved)	58		
NC (Reserved)	56	57	GND
NC	54	55	REFCLKp
CLKREQ# (I/O)(0/3.3V)	52	53	REFCLKn
PERST# (I)(0/3.3V)	50	51	GND
NC	48	49	PERp0
NC	46	47	PERn0
NC	44	45	GND
NC (reserved for SMB_DATA)	42	43	PETp0
NC (reserved for SMB_CLK)	40	41	PETn0
NC	38	39	GND
NC	36	37	PERp1
NC	34	35	PERn1
NC	32	33	GND
NC	30	31	PETp1
NC (reserved for ROM code)	28	29	PETn1
NC	26	27	GND
NC	24	25	PERp2
NC	22	23	PERn2
NC	20	21	GND
3.3V	18	19	PETp2
3.3V	16	17	PETn2
3.3V	14	15	GND

3.3V	12	13	PERp3
LED1#	10	11	PERn3
NC	8	9	GND
NC	6	7	PETp3
3.3V	4	5	PETn3
3.3V	2	3	GND
		1	GND

2.10 Mechanical Dimensions

M.2 Type 2242-D2-M

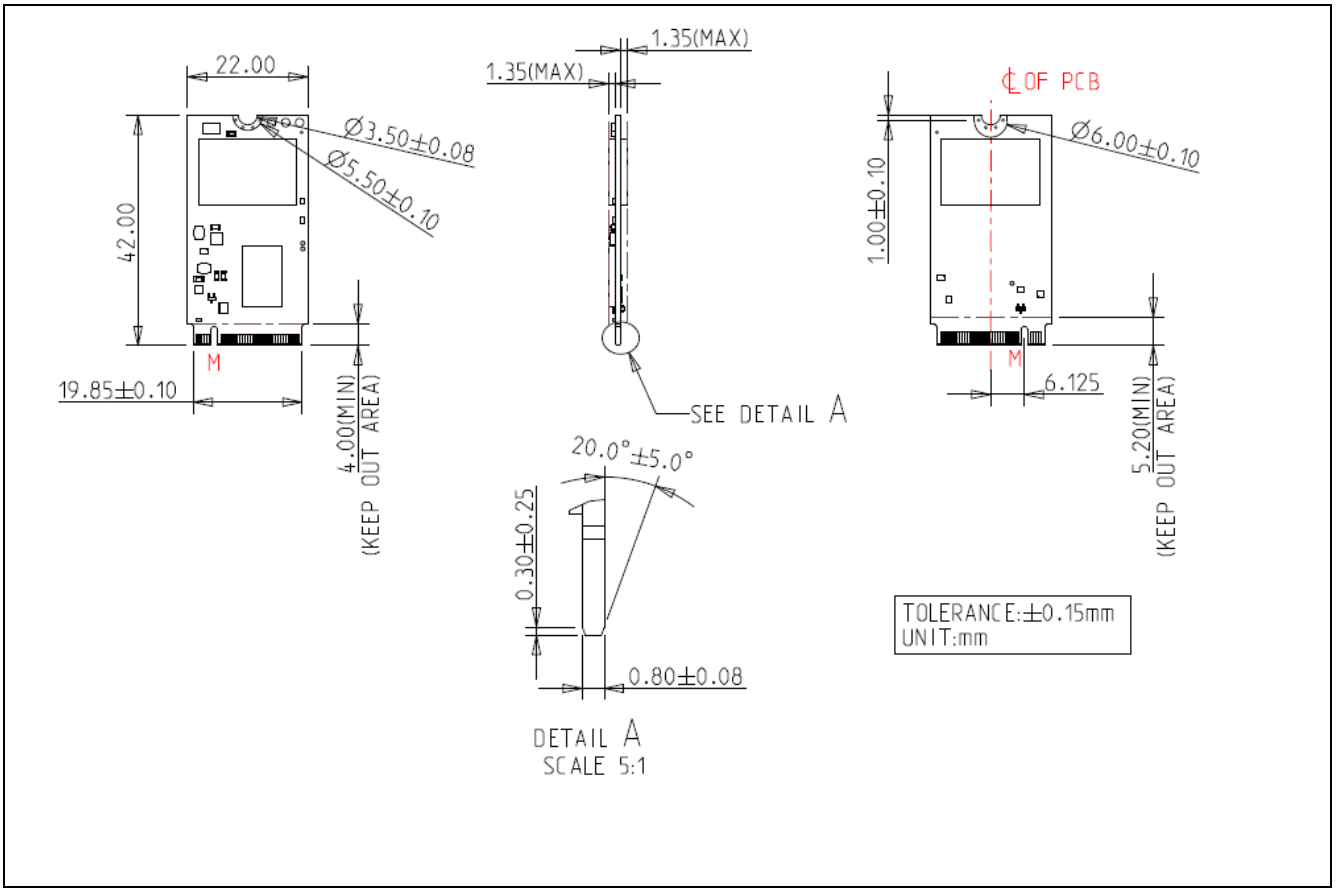


Figure 2: Innodisk M.2 (P42) 3TE6 diagram

2.11 Assembly Weight

An Innodisk M.2 (P42) 3TE6 within NAND flash ICs, 128GB's weight is 7 grams approximately.

2.12 Seek Time

Innodisk M.2 (P42) 3TE6 is not a magnetic rotating design. There is no seek or rotational latency required.

2.13 NAND Flash Memory

Innodisk M.2 (P42) 3TE6 uses industrial 3D TLC NAND flash memory, which is non-volatility, high reliability and high speed memory storage.

2.14 Heat-spreading copper layer

Innodisk M.2 (P42) 3TE6 industry temperature models come with a 2.14 Heat-spreading copper layer installed on top of 3TE6 with dimension of 30x20x0.25 mm. This design will increase 3TE6's height by 0.25-0.4mm due to the thermal pad and copper layer itself.

3. Theory of Operation

3.1 Overview

Figure 2 shows the operation of Innodisk M.2 (P42) 3TE6 from the system level, including the major hardware blocks.

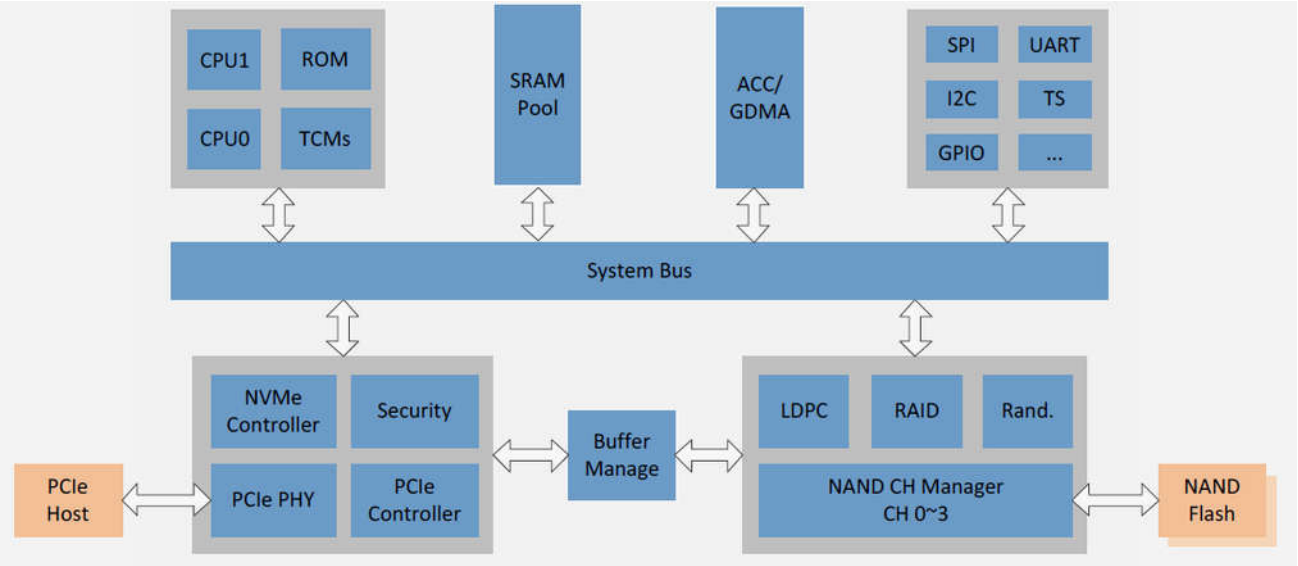


Figure 3: Innodisk M.2 (P42) 3TE6 Block Diagram

Innodisk M.2 (P42) 3TE6 integrates a PCIe Gen III x4 controller and NAND flash memories. Communication with the host occurs through the host interface, using the standard NVM protocol. Communication with the flash device(s) occurs through the flash interface.

3.2 PCIe Gen III x 4 Controller

Innodisk M.2 (P42) 3TE6 is designed with innodisk ID303, a PCIe Gen IIIx4 controller which is compliant with NVMe 1.3, up to 32.0Gbps transfer speed. In addition, it is compliant with PCIe Gen. 1, Gen. 2 and Gen. 3 specification. The controller supports up to four channels for flash interface.

3.3 Error Detection and Correction

Innodisk M.2 (P42) 3TE6 is designed with hardware LDPC ECC engine with hard-decision and soft-decision decoding. Low-density parity-check (LDPC) codes have excellent error correcting performance close to the Shannon limit when decoded with the belief-propagation (BP) algorithm using soft-decision information.

3.4 Wear-Leveling

Flash memory can be erased with a limited number of cycles. This number is called the ***erase cycle limit*** or ***write endurance limit*** and is defined by the flash NAND vendor. The erase cycle limit applies to each individual erase block in the flash device.

Innodisk M.2 (P42) 3TE6 uses a combination of two types of wear leveling- dynamic and static wear leveling- to distribute write cycling across an SSD and balance erase count of each block, thereby extending device lifetime.

3.5 Bad Blocks Management

Bad Blocks are blocks that contain one or more invalid bits whose reliability are not guaranteed. The Bad Blocks may be presented while the SSD is shipped, or may develop during the lifetime of the SSD. When a Bad Block is detected, it will be flagged as unusable block by firmware. The SSD implement Bad Blocks management that consists of Bad Blocks replacement and Error Correcting to avoid data error occurred. The functions will be enabled automatically to transfer data from Bad Blocks to spare blocks, and correct error bit.

3.6 Garbage Collection/TRIM

Garbage collection and TRIM technology is used to maintain data consistency and perform continual data cleansing on SSDs. It runs as a background process, freeing up valuable controller resources while sorting good data into available blocks, and deleting bad blocks. It also significantly reduces write operations to the drive, thereby increasing the SSD's speed and lifespan.

3.7 End to End Data Path Protection

End-to-end Data Path Protection that secures the data transmission between host system and NAND Flash. In the transmission path, no matter in or out, all buffer and storage implement Error Code Correction that optimizes the data integrity in the whole transmission of SSD.

3.8 Thermal Management

M.2 (P42) 3TE6 has built-in thermal sensor which can detect environment temperature of SSD. In the meantime, firmware will monitor the thermal sensor to prevent any failure of overheating. During extreme temperature, firmware will adjust the data transfer behavior to maintain the SSD's reliable operation.

3.9 AES function (Optional)

M.2 (P42) 3TE6 has built-in AES-128/256 hardware encryption engine to encode and decode data to ensure efficiency and data security. In other words, there is no impact on CPU performance, as the controller will handle all encryption and decryption.

4. Installation Requirements

4.1 M.2 (P42) 3TE6 Pin Directions

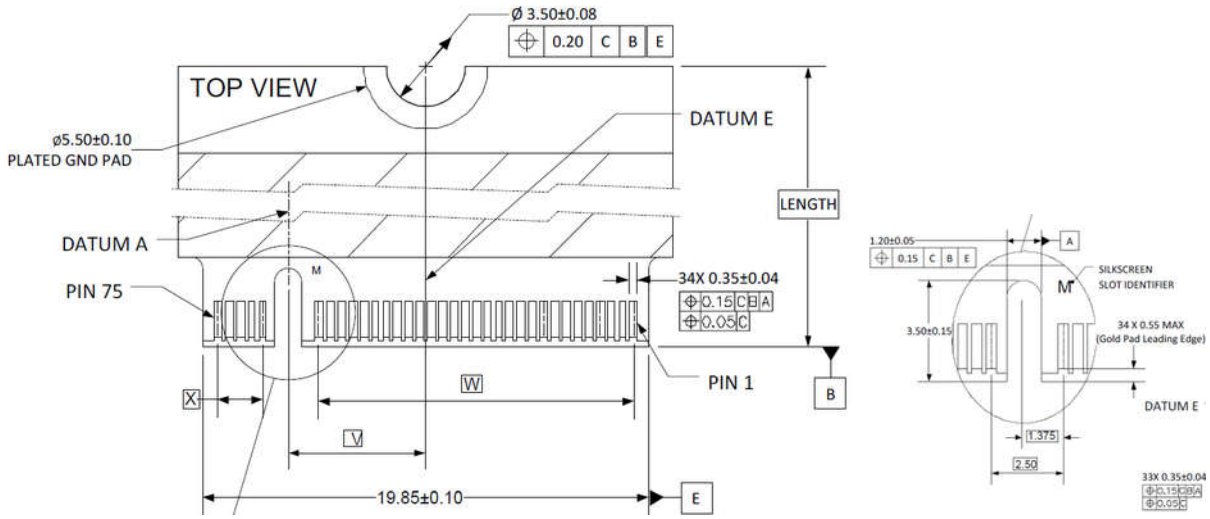


Figure 4: Signal Segment and Power Segment

4.2 Electrical Connections for M.2 (P42) 3TE6

M.2 interconnect is based on a 75 position Edge Card connector. The 75 position connector is intended to be keyed so as to distinguish between families of host interfaces and the various Sockets used in general Platforms. M.2(P42) 3TE6 is compliant with M.2 Socket 2 key M.

4.3 Device Drive

M.2(P42) 3TE6 is compliant with NVMe 1.3. Both Operation System and BIOS should include NVMe driver to compatible with NVMe device. Nowadays, most of OS includes NVMe in-box driver now. For more information about the driver support in each OS, please visit the website http://nvmexpress.org/resources/drivers. For BIOS NVMe driver support please contact with motherboard manufacturers.

5. SMART / Health Information

This log page is used to provide SMART and general health information. The information provided is over the life of the controller and is retained across power cycles. More details about Set Features command; please refer to NVM Express 1.3

5.1 Get Log Page(Log Identifier 02h)

Innodisk 3TE6 series SMART / Health Information Log are listed in following table.

Table 10: Get Log Page – SMART / Health Information Log

<table>
<tr><th>Bytes</th><th>Description</th></tr>
<tr><td>0</td><td>Critical Warning: This field indicates critical warnings for the state of the controller. Each bit corresponds to a critical warning type; multiple bits may be set. If a bit is cleared to ‘0’, then that critical warning does not apply. Critical warnings may result in an asynchronous event notification to the host. Bits in this field represent the current associated state and are not persistent.
<table>
<tr><th>Bit</th><th>Definition</th></tr>
<tr><td>0</td><td>If set to ‘1’, then the available spare space has fallen below the threshold.</td></tr>
<tr><td>1</td><td>If set to ‘1’, then a temperature is above an over temperature threshold or below an under</td></tr>
<tr><td>2</td><td>If set to ‘1’, then the NVM subsystem reliability has been degraded due to significant media related</td></tr>
<tr><td>3</td><td>If set to ‘1’, then the media has been placed in read only mode.</td></tr>
<tr><td>4</td><td>If set to ‘1’, then the volatile memory backup device has failed. This field is only valid if the</td></tr>
<tr><td>7:5</td><td>Reserved</td></tr>
</table></td></tr>
<tr><td>1:2</td><td>Composite Temperature: Contains a value corresponding to a temperature in degrees Kelvin that represents the current composite temperature of the controller and namespace(s) associated with that controller. The manner in which this value is computed is implementation specific and may not represent the actual temperature of any physical point in the NVM subsystem. The value of this field may be used to trigger an asynchronous event.</td></tr>
</table>

	Warning and critical overheating composite temperature threshold values are reported by the WCTEMP and CCTEMP fields in the Identify Controller data structure.
3	**Available Spare:** Contains a normalized percentage (0 to 100%) of the remaining spare capacity available.
4	**Available Spare Threshold:** When the Available Spare falls below the threshold indicated in this field, an asynchronous event completion may occur. The value is indicated as a normalized percentage (0 to 100%).
5	**Percentage Used:** Contains a vendor specific estimate of the percentage of NVM subsystem life used based on the actual usage and the manufacturer's prediction of NVM life. A value of 100 indicates that the estimated endurance of the NVM in the NVM subsystem has been consumed, but may not indicate an NVM subsystem failure. The value is allowed to exceed 100. Percentages greater than 254 shall be represented as 255. This value shall be updated once per power-on hour (when the controller is not in a sleep state). Refer to the JEDEC JESD218A standard for SSD device life and endurance measurement techniques.
6:31	**Reserved**
32:47	**Data Units Read:** Contains the number of 512 byte data units the host has read from the controller; this value does not include metadata. This value is reported in thousands (i.e., a value of 1 corresponds to 1000 units of 512 bytes read) and is rounded up. When the LBA size is a value other than 512 bytes, the controller shall convert the amount of data read to 512 byte units. For the NVM command set, logical blocks read as part of Compare and Read operations shall be included in this value.
48:63	**Data Units Written:** Contains the number of 512 byte data units the host has written to the controller; this value does not include metadata. This value is reported in thousands (i.e., a value of 1 corresponds to 1000 units of 512 bytes written) and is rounded up. When the LBA size is a value other than 512 bytes, the controller shall convert the amount of data written to 512 byte units. For the NVM command set, logical blocks written as part of Write operations shall be included in this value. Write Uncorrectable commands shall not impact this value.
64:79	**Host Read Commands:** Contains the number of read commands completed by the controller. For the NVM command set, this is the number of Compare and Read commands.

80:95	**Host Write Commands:** Contains the number of write commands completed by the controller. For the NVM command set, this is the number of Write commands.
96:111	**Controller Busy Time:** Contains the amount of time the controller is busy with I/O commands. The controller is busy when there is a command outstanding to an I/O Queue (specifically, a command was issued via an I/O Submission Queue Tail doorbell write and the corresponding completion queue entry has not been posted yet to the associated I/O Completion Queue). This value is reported in minutes.
112:127	**Power Cycles:** Contains the number of power cycles.
128:143	**Power On Hours:** Contains the number of power-on hours. This may not include time that the controller was powered and in a non-operational power state.
144:159	**Unsafe Shutdowns:** Contains the number of unsafe shutdowns. This count is incremented when a shutdown notification (CC.SHN) is not received prior to loss of power.
160:175	**Media and Data Integrity Errors:** Contains the number of occurrences where the controller detected an unrecovered data integrity error. Errors such as uncorrectable ECC, CRC checksum failure, or LBA tag mismatch are included in this field.
176:191	**Number of Error Information Log Entries:** Contains the number of Error Information log entries over the life of the controller.
192:195	**Warning Composite Temperature Time:** Contains the amount of time in minutes that the controller is operational and the Composite Temperature is greater than or equal to the Warning Composite Temperature Threshold (WCTEMP) field and less than the Critical Composite Temperature Threshold (CCTEMP) field in the Identify Controller data structure. If the value of the WCTEMP or CCTEMP field is 0h, then this field is always cleared to 0h regardless of the Composite Temperature value.
196:199	**Critical Composite Temperature Time:** Contains the amount of time in minutes that the controller is operational and the Composite Temperature is greater than the Critical Composite Temperature Threshold (CCTEMP) field in the Identify Controller data structure. If the value of the CCTEMP field is 0h, then this field is always cleared to 0h regardless of the Composite Temperature value.
200:201	**Temperature Sensor 1:** Contains the current temperature reported by controller's temperature sensor.
202:203	**Temperature Sensor 2:** Contains the current temperature reported by external temperature sensor.

204:205	**Temperature Sensor 3:** Contains the current temperature reported by channel zero CE zero NAND's temperature sensor.
206:207	**Temperature Sensor 4:** Contains the current temperature reported by last channel CE zero NAND's temperature sensor.
208:209	**Temperature Sensor 5:** Contains the current temperature reported by temperature sensor 5.
210:211	**Temperature Sensor 6:** Contains the current temperature reported by temperature sensor 6.
212:213	**Temperature Sensor 7:** Contains the current temperature reported by temperature sensor 7.
214:215	**Temperature Sensor 8:** Contains the current temperature reported by temperature sensor 8.
216:219	**Thermal Management Temperature 1 Transition Count:** Lower Power Active Power States or Performed Vendor Specific Thermal Management
220:223	**Thermal Management Temperature 2 Transition Count:** Lower Power Active Power States or Performed Vendor Specific Thermal Management
224:227	**Total Time For Thermal Management Temperature 1:** Duration in Lower Power Active Power States or Performed Vendor Specific Thermal Management
228:231	**Total Time For Thermal Management Temperature 2:** Duration in Lower Power Active Power States or Performed Vendor Specific Thermal Management
232:337	**Reserved**
338:345	**Later Bad Count**
346:353	**Power-On hours Count**
354:361	**Drive Power Cycle Count**
362:369	**Total Bad Block Count**
370:377	**User Max Erase Count**
378:385	**User Avg Erase Count**
386:393	**Device Life**
394:401	**Spare Block Count**
402:409	**Program Fail Count**
410:417	**Erase Fail Count**
418:425	**Unexpected Power Loss Count**

426:433	**Temperature (Kelvin - K °K)**
434:441	**Flash ID**
442:449	**Later Bad Block Info (Read / Write / Erase)**
450:457	**Total LBAs Written (uint = 32MB)**
458:465	**Total LBAs Read (uint = 32MB)**

6. Part Number Rule

CODE	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20
	D	**E**	**M**	**2**	**4**	**-**	**A**	**2**	**8**	**D**	**D**	**1**	**E**	**C**	**A**	**D**	**F**	**-**	**X**	**X**

Definition

Code 1st (Disk)			**Code 14th (Operation Temperature)**
D : Disk			C: Standard Grade (0℃~ +70℃)
Code 2nd (Feature set)			W: Industrial Grade (-40℃~ +85℃)
E : Embedded series			
Code 3rd ~5th (Form factor)			**Code 15th (Internal control)**
M24: M.2 Type 2242-D2-M			A~Z: BGA PCB version.
Code 7th ~9th (Capacity)			**Code 16th (Channel of data transfer)**
64G: 64GB	A28: 128GB	B56: 256GB	D: Dual Channels
C12: 512GB			Q: Quad Channels
Code 10th ~12th (Controller)			**Code 17th (Flash Type)**
DD1: ID303 PCIe3.0x4			F: Kioxia 64 layer 3D TLC
DD2: ID303 with AES PCIe3.0x4			H: Kioxia 96 layer 3D TLC
Code 13th (Flash mode)			**Code 18th ~20th (Customize code)**
E: 64 Layer 3D TLC G: 96 Layer 3D TLC			

7. Appendix

REACH

innodisk

宜鼎國際股份有限公司
Innodisk Corporation

Tel:(02)7703-3000 Fax:(02) 7703-3555 Internet: http://www.innodisk.com/

REACH Declaration of Conformity

Manufacturer Product: All Innodisk EM Flash and Dram products

1. 宜鼎國際股份有限公司（以下稱本公司）特此保證此售予貴公司之產品，皆符合歐盟化學品法案(Registration , Evaluation and Authorization of Chemicals : (EC) No 1907/2006 REACH)以及附錄 XIV 中的限用物質之規定 (http://www.echa.europa.eu/de/candidate-list-table **last updated: 12/01/2017，SVHC's 173)**。
所提供之產品包含：(1) 產品或產品所使用到的所有原物料；(2)包裝材料；(3)設計、生產及重工過程中所使用到的所有原物料。
We Innodisk Corporation hereby declare that our products are in compliance with the requirements according to the (EC) No 1907/2006 REACH Regulation and restricted substances in Annex XIV (http://www.echa.europa.eu/de/candidate-list-table **last updated: 12/01/2017，SVHC's 173).**
Products include： 1) Product and raw material used by the product；2) Packaging material ；3) Raw material used in the process of design, production and rework.
2. 本公司同意因本保證書或與本保證書相關事宜有所爭議時，雙方宜友好協商，達成協議。
InnoDisk Corporation agrees that both parties shall settle any dispute arising from or in connection with this Declaration of Conformity by friendly negotiations.

立 保 證 書 人 (Guarantor)

Company name 公司名稱： InnoDisk Corporation 宜鼎國際股份有限公司

Company Representative 公司代表人： Randy Chien 簡川勝

Company Representative Title 公司代表人職稱： Chairman 董事長

Date 日期： 2017 / 02 / 08

RoHS

宜鼎國際股份有限公司
Innodisk Corporation

Tel:(02)7703-3000 Fax:(02) 7703-3555 Internet: http://www.innodisk.com/

RoHS 自我宣告書(RoHS Declaration of Conformity)

Manufacturer Product: All Innodisk EP products

一、 宜鼎國際股份有限公司（以下稱本公司）特此保證售予貴公司之所有產品，皆符合歐盟 2011/65/EU 及(EU) 2015/863 關於 RoHS 之規範要求。

Innodisk Corporation declares that all products sold to the company, are complied with European Union RoHS Directive (2011/65/EU) and (EU) 2015/863 requirement.

二、 本公司同意因本保證書或與本保證書相關事宜有所爭議時，雙方宜友好協商，達成協議。

Innodisk Corporation agrees that both parties shall settle any dispute arising from or in connection with this Declaration of Conformity by friendly negotiations.

Name of hazardous substance	Limited of RoHS ppm (mg/kg)
鉛 (Pb)	< 1000 ppm
汞 (Hg)	< 1000 ppm
鎘 (Cd)	< 100 ppm
六價鉻 (Cr 6+)	< 1000 ppm
多溴聯苯 (PBBs)	< 1000 ppm
多溴二苯醚 (PBDEs)	< 1000 ppm
鄰苯二甲酸二(2-乙基己基)酯 (DEHP)	< 1000 ppm
鄰苯二甲酸丁酯苯甲酯 (BBP)	< 1000 ppm
鄰苯二甲酸二丁酯 (DBP)	< 1000 ppm
鄰苯二甲酸二異丁酯 (DIBP)	< 1000 ppm

立 保 證 書 人 (Guarantor)

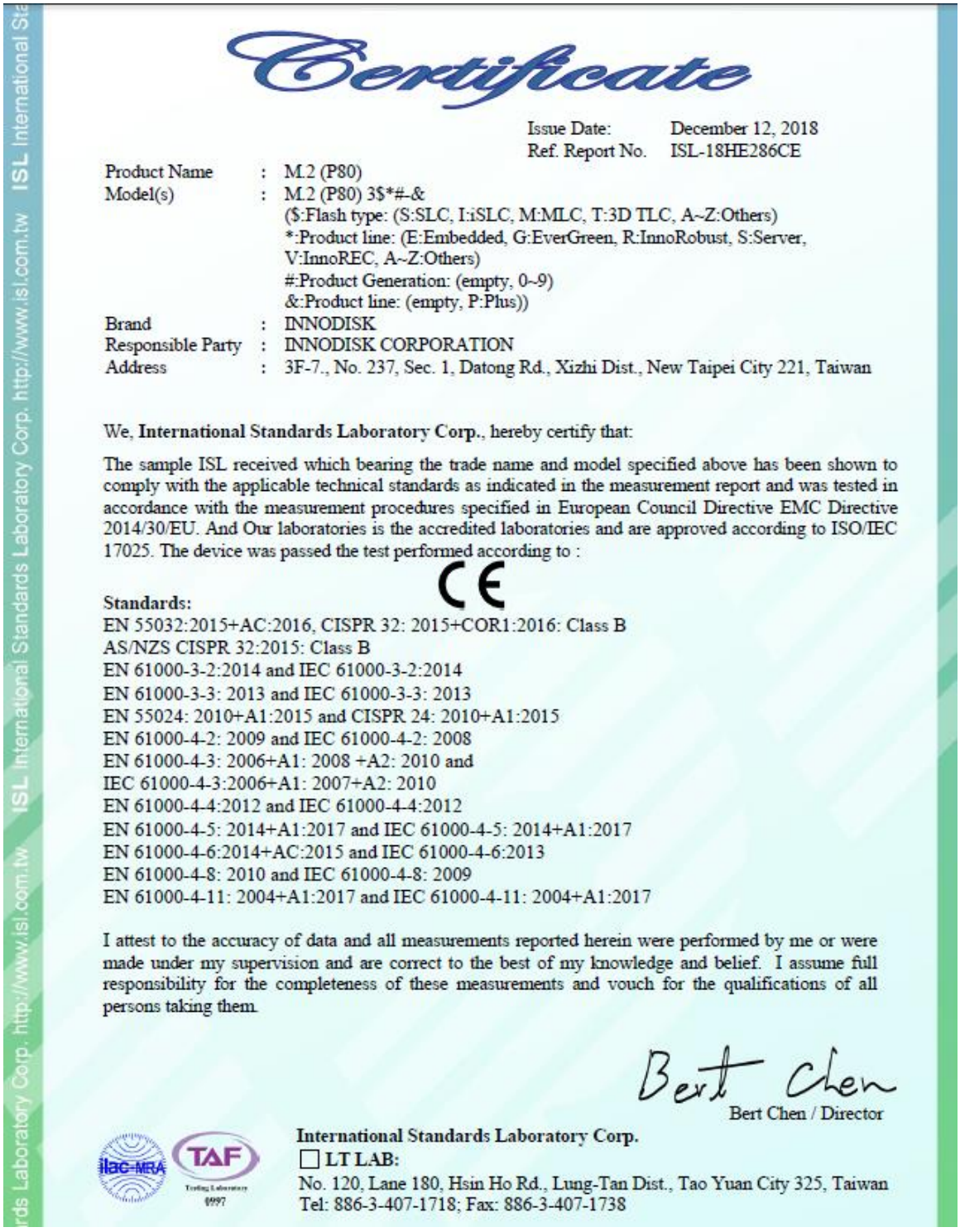
Company name 公司名稱： Innodisk Corporation 宜鼎國際股份有限公司

Company Representative 公司代表人： Randy Chien 簡川勝

Company Representative Title 公司代表人職稱： Chairman 董事長

Date 日期： 2018 / 07 / 01

CE



Certificate

Issue Date: December 12, 2018
Ref. Report No. ISL-18HE286CE

Product Name	:	M.2 (P80)
Model(s)	:	M.2 (P80) 3$*#-& ($:Flash type: (S:SLC, I:iSLC, M:MLC, T:3D TLC, A~Z:Others) *:Product line: (E:Embedded, G:EverGreen, R:InnoRobust, S:Server, V:InnoREC, A~Z:Others) #:Product Generation: (empty, 0~9) &:Product line: (empty, P:Plus))
Brand	:	INNODISK
Responsible Party	:	INNODISK CORPORATION
Address	:	3F-7., No. 237, Sec. 1, Datong Rd., Xizhi Dist., New Taipei City 221, Taiwan

We, **International Standards Laboratory Corp.**, hereby certify that:

The sample ISL received which bearing the trade name and model specified above has been shown to comply with the applicable technical standards as indicated in the measurement report and was tested in accordance with the measurement procedures specified in European Council Directive EMC Directive 2014/30/EU. And Our laboratories is the accredited laboratories and are approved according to ISO/IEC 17025. The device was passed the test performed according to :

CE

Standards:
EN 55032:2015+AC:2016, CISPR 32: 2015+COR1:2016: Class B
AS/NZS CISPR 32:2015: Class B
EN 61000-3-2:2014 and IEC 61000-3-2:2014
EN 61000-3-3: 2013 and IEC 61000-3-3: 2013
EN 55024: 2010+A1:2015 and CISPR 24: 2010+A1:2015
EN 61000-4-2: 2009 and IEC 61000-4-2: 2008
EN 61000-4-3: 2006+A1: 2008 +A2: 2010 and
IEC 61000-4-3:2006+A1: 2007+A2: 2010
EN 61000-4-4:2012 and IEC 61000-4-4:2012
EN 61000-4-5: 2014+A1:2017 and IEC 61000-4-5: 2014+A1:2017
EN 61000-4-6:2014+AC:2015 and IEC 61000-4-6:2013
EN 61000-4-8: 2010 and IEC 61000-4-8: 2009
EN 61000-4-11: 2004+A1:2017 and IEC 61000-4-11: 2004+A1:2017

I attest to the accuracy of data and all measurements reported herein were performed by me or were made under my supervision and are correct to the best of my knowledge and belief. I assume full responsibility for the completeness of these measurements and vouch for the qualifications of all persons taking them.

Bert Chen

Bert Chen / Director

International Standards Laboratory Corp.
☐ **LT LAB:**
No. 120, Lane 180, Hsin Ho Rd., Lung-Tan Dist., Tao Yuan City 325, Taiwan
Tel: 886-3-407-1718; Fax: 886-3-407-1738

FCC



Certificate

Issue Date: December 12, 2018
Ref. Report No. ISL-18HE286FB

Product Name	:	M.2 (P80)
Model(s)	:	M.2 (P80) 3$*#-& ($:Flash type: (S:SLC, I:iSLC, M:MLC, T:3D TLC, A~Z:Others) *:Product line: (E:Embedded, G:EverGreen, R:InnoRobust, S:Server, V:InnoREC, A~Z:Others) #:Product Generation: (empty, 0~9) &:Product line: (empty, P:Plus))
Brand	:	INNODISK
Applicant	:	INNODISK CORPORATION
Address	:	3F-7., No. 237, Sec. 1, Datong Rd., Xizhi Dist., New Taipei City 221, Taiwan

We, **International Standards Laboratory Corp.**, hereby certify that:

The sample ISL received which bearing the trade name and model specified above has shown to comply with the applicable technical standards as indicated in the measurement report and was tested in accordance with the measurement procedures specified. (refer to Test Report if any modifications were made for compliance). And Our laboratories is the accredited laboratories and are approved according to ISO/IEC 17025.

Standards:

FCC CFR Title 47 Part 15 Subpart B: Section 15.107 and 15.109
ANSI C63.4-2014
Industry Canada Interference-Causing Equipment Standard ICES-003 Issue 6: 2016
Class B

I attest to the accuracy of data and all measurements reported herein were performed by me or were made under my supervision and are correct to the best of my knowledge and belief. I assume full responsibility for the completeness of these measurements and vouch for the qualifications of all persons taking them.

Bert Chen

Bert Chen / Director

International Standards Laboratory Corp.
☐ **LT LAB:**
No. 120, Lane 180, Hsin Ho Rd., Lung-Tan Dist., Tao Yuan City 325, Taiwan
Tel: 886-3-407-1718; Fax: 886-3-407-1738

MSL Statement

MSL Declaration of Conformity

1. Purpose: MSL (Moisture Sensitivity Levels) specification statement for all Innodisk products

2. Scope: For all Innodisk products

3. Reference:

4.1 JEDEC, J-STD-020

4.2 JEDEC, J-STD-033

4. Description

5.1 Innodisk Products MSL Level:

Flash /DRAM Module Level 1

BGA IC (nanoSSD family) Level 3

5.2 Floor Life Time: Refer following table

		Soak Requirements				
	Floor Life		Standard		Accelerated	
Level	Time	Cond degC/%RH	Time (hrs)	Cond degC/%RH	Time (hrs)	Cond degC/%RH
1	unlimited	<=30/85%	168+5/-0	85/85	n/a	n/a
2	1 year	<=30/60%	168+5/-0	85/60	n/a	n/a
2a	4 weeks	<=30/60%	696+5/-0	30/60	120+1/-0	60/60
3	168 hours	<=30/60%	192+5/-0	30/60	40+1/-0	60/60
4	72 hours	<=30/60%	96+2/-0	30/60	20+0.5/-0	60/60
5	48 hours	<=30/60%	72+2/-0	30/60	15+0.5/-0	60/60
5a	24 hours	<=30/60%	48+2/-0	30/60	10+0.5/-0	60/60
6	TOL	<=30/60%	TOL	30/60	n/a	60/60

Innodisk Corporation
Quality Assurance Div
Manager
Yi Chuan Chen
Date: 2018.09.27



數位簽章者：Yi Chuan Chen
DN：cn=Yi Chuan Chen, o=Innodisk Corporation, ou=QA Div, email=yichuan_chen@innodisk.com, c=TW
日期：2018.09.27 10:41:58 +08'00'

Headquarter (Taiwan) : HTTP://WWW.INNODISK.COM E-MAIL: SALES@INNODISK.COM
TEL: +886-2-7703-3000 ADD: 5F, No. 237, Sec. 1, Datong Rd., Xizhi Dist., New Taipei City 221, Taiwan(R.O.C.)
USA Office: usasales@InnoDisk.com / Europe: eusales@InnoDisk.com / Japan: jpsales@InnoDisk.com / China: sales_cn@InnoDisk.com

1